

## REMARKS

### *Claim Rejections under 35 U.S.C. § 112*

Claim 10 stands rejected under 35 U.S.C. § 112, second paragraph as being indefinite. Namely, the examiner asserts that the term “the thicker covering” has no antecedent basis. This rejection is respectfully traversed.

Claim 10 recites “said temporary covering being thicker in said first trench than over said semiconductor structure.” Claim 10 also recites “said temporary covering having an opening through a thinner portion of said temporary covering that is over said semiconductor structure.” Thus, the temporary covering is thicker *in* the first trench and is thinner over the semiconductor structure. Thus, where claim 10 recites, “said thinner portion other than *the thicker* temporary covering *in* said first trench” it is clear that the thicker temporary covering refers to the thicker temporary covering that is *in* the first trench. There is no other thicker temporary covering. Reconsideration of the rejection is requested.

### *Claim Rejections under 35 U.S.C. § 102*

Claim 10 has been amended to call for a temporary covering. Nishida’s insulating film 106 is not temporary—it is what isolates regions. Column 1, lines 12-14; Figure 7. Thus, Nishida does not anticipate.

### *Claim Rejections under 35 U.S.C. § 103*

The rejection of claim 21 is respectfully traversed. The examiner asserts that it would have been obvious to incorporate the teachings of Wen into the device of Nishida to reduce the leakage current for the structure. But unlike Nishida, Wen’s trenches as a whole do not isolate adjacent transistors.

For example, Nishida’s isolation regions might be used to isolate adjacent transistors. *See, e.g.*, column 1, lines 33-64; Figure 13. In contrast, Wen’s trenches form the source, drain, and gate of transistors. Column 1, lines 9-16. Only a thin layer isolation oxide 21 is formed in the deep trench to reduce leakage current—the remainder of the deep trench is filled with heavily doped polysilicon to form the source and drain of a transistor. Column 3, lines 26-53. Thus, Wen forms transistors with his trenches whereas Nishida isolates transistors with his. As the purposes of the trenches as a whole teach away from each other, there is no reason to modify Nishida in view of Wen. Reconsideration is requested.

The application is in condition for allowance. The examiner's prompt action in accordance therewith is requested.

Respectfully submitted,

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A handwritten signature in cursive script, appearing to read "Rhonda L. Sheldon", is written over a horizontal line.

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